

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	I <sub>D</sub>	7.63 4.92	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	30	A

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.16	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	R <sub>0JA</sub>	107.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

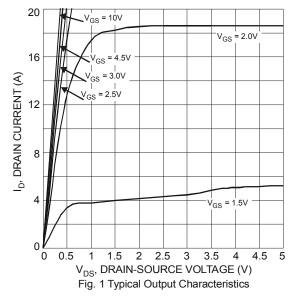
### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

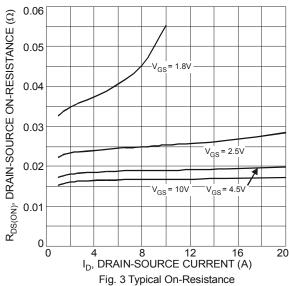
	T						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	l	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.2	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	l	19	28	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Static Dialii-Source Off-Resistance			25	41		$V_{GS} = 2.5V, I_D = 5.2A$	
Forward Transfer Admittance	Y <sub>fs</sub>		6	_	S	$V_{DS} = 10V, I_{D} = 6A$	
Diode Forward Voltage	$V_{SD}$	l	0.7	1.2	<b>V</b>	$V_{GS} = 0V, I_{S} = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	l	550		pF	V <sub>DS</sub> =10V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	l	88				
Reverse Transfer Capacitance	Crss	l	81				
Gate Resistance	Rg	l	1.34		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	l	15.6		nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$	
Total Gate Charge	Qg	l	7.2		V = 45 V V = 40 V		
Gate-Source Charge	Qgs	_	1	_	nC	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10V,	
Gate-Drain Charge	Q <sub>gd</sub>	_	1.9	_		$I_D = 6A$	
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.69	_			
Turn-On Rise Time	t <sub>r</sub>	-	13.19	_	20	$V_{DD} = 10V, V_{GEN} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	1	22.1	_	ns	$R_g = 1\Omega, I_D = 6.7A$	
Turn-Off Fall Time	t <sub>f</sub>	_	6.43	_			

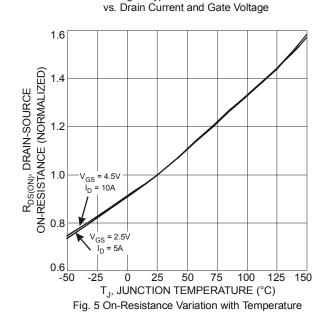
Notes:

- Device mounted on FR-4 PCB with minimum recommended pad layout.
  Repetitive rating, pulse width limited by function temperature.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.









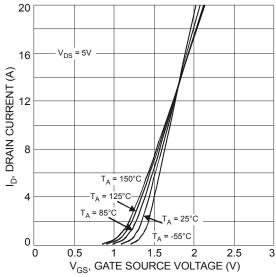


Fig. 2 Typical Transfer Characteristics

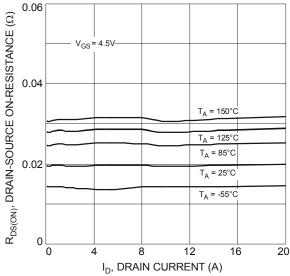


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

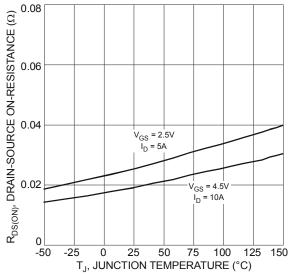


Fig. 6 On-Resistance Variation with Temperature



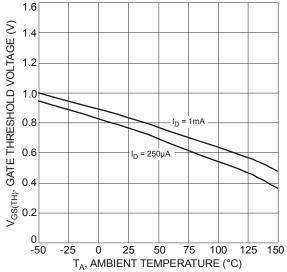
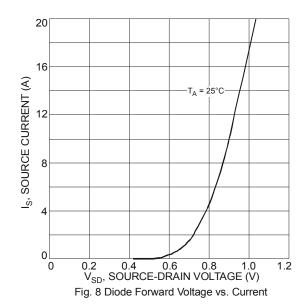
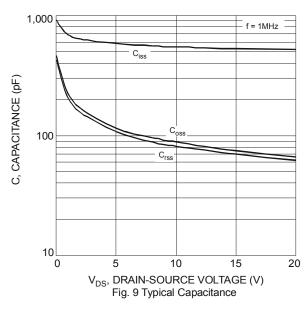
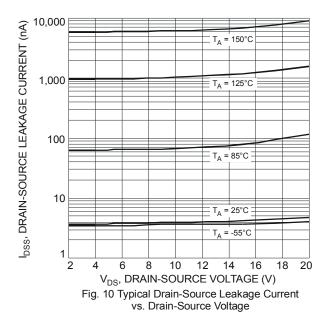
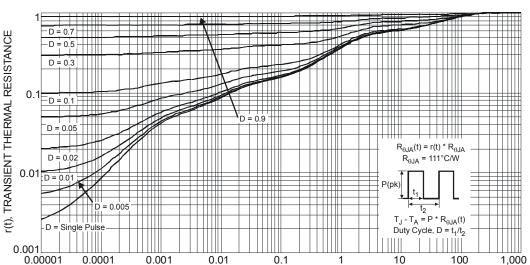


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







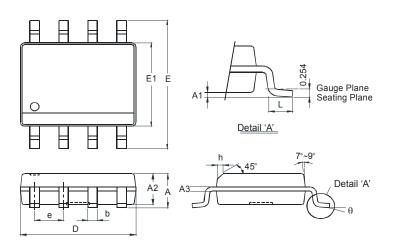


t<sub>1</sub>, PULSE DURATION TIME (s)Fig. 11 Transient Thermal Response



### **Package Outline Dimensions**

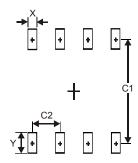
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Υ	1.55
C1	5.4
C2	1.27



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